



<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT(S)</b> (Use as many sheets as necessary)	<b>Form 1449/PTO</b>		<b>COMPLETE IF KNOWN</b>	
	Application Number		10/533,822	
	Filing Date		August 31, 2005	
	First Named Inventor		Mino Green	
	Art Unit		2815	
	Examiner Name		Jami M. Valentine	
Sheet 1 of 3		Attorney Docket No.		KSTR 2 00004

U.S. PATENT DOCUMENTS				
Examiner Initials*	Cite No.	Document No. Number-Kind Code (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
	AA	US-		

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No.	Foreign Patent Document Country Code-Number Kind Code (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	T
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OTHER -- NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published			T
	AC	Ohara et al, "A thin film silicon...", J. Power Sources 136 (2004), pp303-6			
	AD	J.P. Maranchi et al, Interfacial properties of the....", J. Electrochem. Soc. 153(6) A1246, 2006			
	AE	M. Green et al, "Structured Silicon Anodes for...", Electrochem and solid-state Letters 6, A75-79, 2003			
	AF	W.-R. Liu et al. Effect of electrode structure on performance of Si anode in Li-ion batteries: Si particle size and conductive additive Journal of Power Sources 140 (2005) 139-144			
	AG	Y. Liu et al. A novel method of fabricating porous silicon material: ultrasonically enhanced anodic electrochemical etching. Solid State Communications 127 (2003) 583-588			
	AH	W. Lang. Silicon Micromachining Technology. Materials Science and Engineering R17 (1996) 1-55			
	AI	T. Qiu et al, From Si nanotubes to nanowires: Synthesis, characterization, and self-assembly, Journal of Crystal Growth 277 (2005) 143-148			
	AJ	K. W. Kolasinski, Silicon nanostructures from electroless electrochemical etching, Current Opinion in Solid State and Materials Science 9 (2005) 73-83			
	AK	X. Badel et al. Formation of ordered pore arrays at the nanoscale by electrochemical etching of n-type silicon. Superlattices and Microstructures 36 (2004) 245-253			
	AL	P. Kleimann et al. Formation of wide and deep pores in silicon by electrochemical etching. Materials Science and Engineering B69-70 (2000) 29-33			
	AM	H.-C. Shin et al. Porous silicon negative electrodes for rechargeable lithium batteries, Journal of Power Sources 139 (2005) 314-320			
	AN	K. Tokoro, D. Uchikawa, M. Shikida, and K. Sato. Anisotropic Etching Properties of Silicon in KOH and TMAH Solutions. Proceedings of the 1998 International Symposium on Micromechatronics and Human Science, 1998. MHS '98. 25-28 Nov. 1998 pp. 65 - 70			

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	BC	S-H Kim, S-H Lee, H-T Lim, Y-K Kim, S-K Lee. (110) silicon etching for high aspect ratio comb structures 1997 6th International Conference on Emerging Technologies and Factory Automation Proceedings, 1997. ETFA '97., 9-12 Sept. 1997 pp.248-252	
	BD	T. Nakahata, H. Nakajima, "Fabrication of lotus-type porous silicon by unidirectional solidification in hydrogen", Materials Science and Engineering A 384 (2004) 373-376	
	BE	Jyh-Woei Lu et al., "A study of the mechanisms of erosion in silicon single crystals using Hertzian fracture tests", Wear 186-187 (1995) 105-116	
	BF	J. B. Chang et al, "Ultrafast growth of single-crystalline Si nanowires", Materials Letters 60 (2006) 2125-2128	
	BG	R. Wagner, W. Ellis. "Vapor-liquid solid mechanism of single crystal growth", Applied Physics Letters Vol4, No.5 March 1964, 89-90	
	BH	X. Q. Yan et al., "H <sub>2</sub> -assisted control growth...", / Journal of Crystal Growth 257 (2003) 69-74	
	BI	Y. Zhang et al., "Synthesis of thin Si whiskers...", Journal of Crystal Growth 186 226 (2001) 185-191	
	BJ	Y. F. Zhang et al. Bulk-quantity Si nanowires synthesized by SiO sublimation. Journal of Crystal Growth 212 (2000) 115-118	
	BK	Z. Jianfeng, Large-scale array of highly oriented silicon-rich micro/nanowires induced by gas flow steering, Solid State Communications 133 (2005) 271-275	
	BL	L. Z. Pei et al, Silicon nanowires grown from silicon monoxide under hydrothermal conditions, Journal of Crystal Growth 289 (2006) 423-427	
	BM	H.F. Yan et al., "Growth of amorphous silicon...", Chemical Physics Letters 323 (2000) 224-228	

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	CC	Y.Y. Wong et al., "Controlled growth of silicon...", Science and Technology of Advanced Materials 6 (2005) 330-4			
	CD	Z.Y. Zhang et al. Catalytic growth of a-FeSi <sub>2</sub> and silicon nanowires. Journal of Crystal Growth 280 288 (2005) 286-291			
	CE	J.W. Kim et al. Improvement of silicon powder negative electrodes by copper electroless deposition for lithium secondary batteries. Journal of Power Sources 147 (2005) 227-233			
	CF	M. Yoshio et al. Electrochemical behaviors of silicon based anode material. Journal of Power Sources 153 (2006) 375-379			
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